2SD874, 2SD874A

Silicon NPN epitaxial planer type

For low-frequency power amplification

Complementary to 2SB766 and 2SB766A

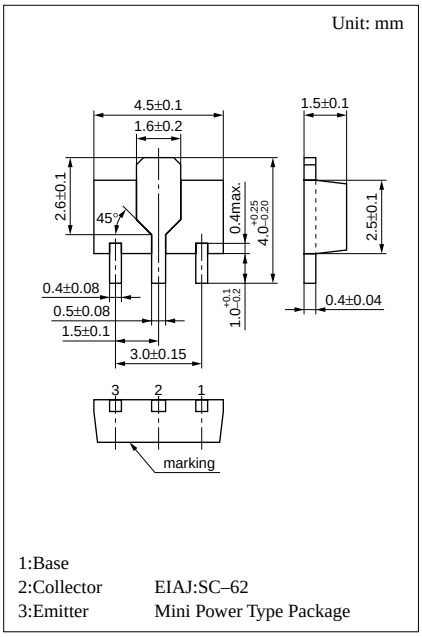
Features

- Large collector power dissipation P_C.
- Low collector to emitter saturation voltage $V_{CE(sat)}$.
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings (Ta=25˚C)

Parameter		Symbol	Ratings	Unit
Collector to base voltage	2SD874	V_{CBO}	30	V
	2SD874A		60	
Collector to emitter voltage	2SD874	V_{CEO}	25	V
	2SD874A		50	
Emitter to base voltage		V_{EBO}	5	V
Peak collector current		I_{CP}	1.5	A
Collector current		I_C	1	A
Collector power dissipation		P_C*	1	W
Junction temperature		T_j	150	˚C
Storage temperature		T_{stg}	–55 ~ +150	˚C

* Printed circuit board: Copper foil area of 1cm^2 or more, and the board thickness of 1.7mm for the collector portion



Marking symbol : Z(2SD874)
Y(2SD874A)

Electrical Characteristics (Ta=25˚C)

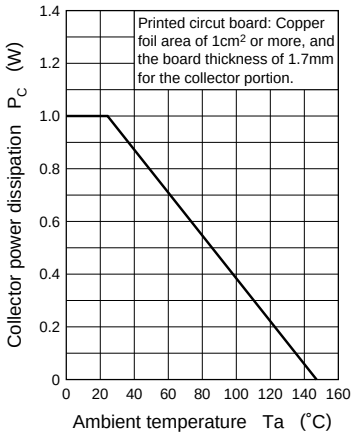
Parameter		Symbol	Conditions	min	typ	max	Unit
Collector cutoff current		I_{CBO}	V_{CB} = 20V, I_E = 0			0.1	μA
Collector to base voltage	2SD874	V_{CBO}	I_C = 10μA, I_E = 0	30			V
	2SD874A			60			
Collector to emitter voltage	2SD874	V_{CEO}	I_C = 2mA, I_B = 0	25			V
	2SD874A			50			
Emitter to base voltage		V_{EBO}	I_E = 10μA, I_C = 0	5			V
Forward current transfer ratio		h_{FE1}*1	V_{CE} = 10V, I_C = 500mA*2	85	160	340	
		h_{FE2}	V_{CE} = 5V, I_C = 1A*2	50			
Collector to emitter saturation voltage		$V_{CE(sat)}$	I_C = 500mA, I_B = 50mA*2		0.2	0.4	V
Base to emitter saturation voltage		$V_{BE(sat)}$	I_C = 500mA, I_B = 50mA*2		0.85	1.2	V
Transition frequency		f_T	V_{CB} = 10V, I_E = –50mA, f = 200MHz		200		MHz
Collector output capacitance		C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz			20	pF

*1 h_{FE1} Rank classification

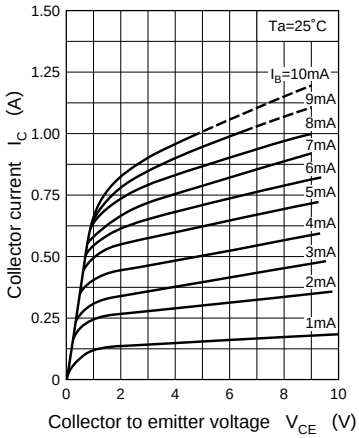
*2 Pulse measurement

Rank		Q	R	S
h_{FE1}		85 ~ 170	120 ~ 240	170 ~ 340
Marking Symbol	2SD874	ZQ	ZR	ZS
	2SD874A	YQ	YR	YS

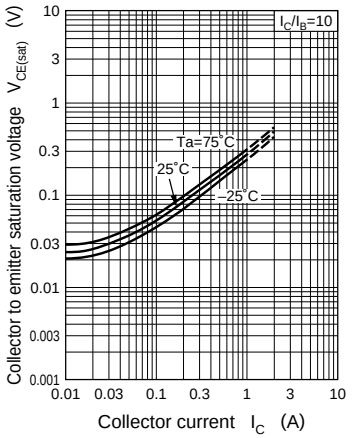
P_C — Ta



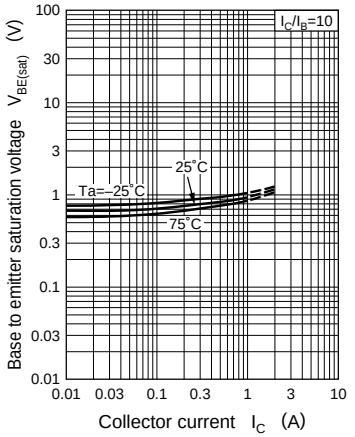
I_C — V_{CE}



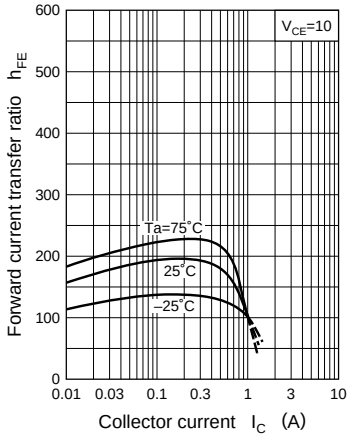
$V_{CE(sat)}$ — I_C



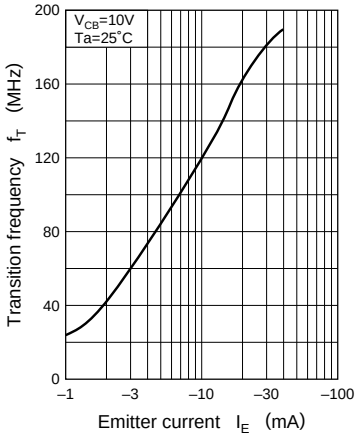
$V_{BE(sat)}$ — I_C



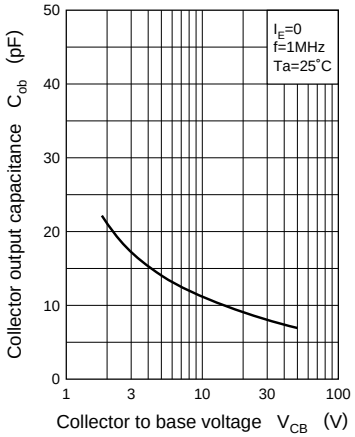
h_{FE} — I_C



f_T — I_E



C_{ob} — V_{CB}



Area of safe operation (ASO)